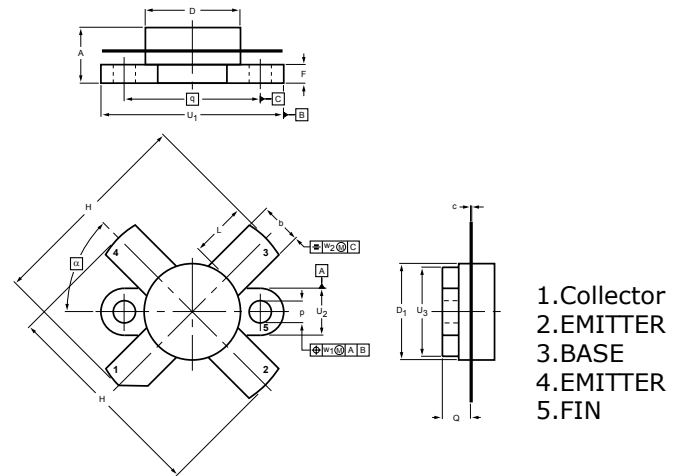


DESCRIPTION

Designed primarily for SSB high amplifier from 2.0 to 30 MHz.

FEATURES

- Output Power: 175W(Typ)
- Power Gain: 11.5 dB Min@28M, 28V
- Efficiency: 40% Min@28M, 28V
- Intermodulation Distortion: -30dB Max@28M, 28V


DIMENSIONS

NOTE: ALL ELECTRODES ARE ISOLATED FROM FLANGE.

UNIT	A	b	c	D	D ₁	F	H	L	p	Q	q	U ₁	U ₂	U ₃	w ₁	w ₂	α
mm	7.27	5.82	0.16	12.86	12.83	2.67	28.45	7.93	3.30	4.45	18.42	24.90	6.48	12.32	0.51	1.02	45°
	6.17	5.56	0.10	12.59	12.57	2.41	25.52	6.32	3.05	3.91		24.63	6.22	12.06			
inches	0.286	0.229	0.006	0.506	0.505	0.105	1.120	0.312	0.130	0.175	0.725	0.98	0.255	0.485	0.02	0.04	
	0.243	0.219	0.004	0.496	0.495	0.095	1.005	0.249	0.120	0.154		0.97	0.245	0.475			

MAXIMUM RATINGS

CHARACTERISTICS	SYMBOL	RATINGS	UNITS
Collector-Base Voltage	V _{CB0}	65	V
Collector-Emitter Voltage	V _{CES}	65	V
Collector-Emitter Voltage	V _{CEO}	40	V
Collector Current Peak	I _{CM}	50	A
Emitter-Base Voltage	V _{EBO}	4	V
Collector Power Dissipation	P _{DISS}	250	W
Junction Temperature	T _J	175	°C
Storage Temperature Range	T _{STG}	-65 to 175	°C

ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX	UNITS
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =100mA, I _B =0	40	-	-	V
Collector-Emitter Breakdown Voltage	V _{(BR)CES}	I _C =100mA, V _{EB} =0	65	-	-	V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E =1mA, I _C =0	4	-	-	V
Collector Cutoff Current	I _{CB0}	V _{CB} =60V, I _E =0	-	-	1	mA
DC Current Gain	h _{FE}	V _{CE} =5V, I _C =10A	10	-	-	
Collector Output Capacitance	C _{Ob}	V _{CB} =28V, I _E =0 f=1MHz	-	480	-	pF
Power Gain	G _P	V _{CC} =28V, P _{OUT} =175W, I _{CQ} =100mA, f=28M, 28.001MHz	11.5	13.0	-	dB
Collector Efficiency	η _C		40	-	-	%
Input Power	P _i		-	7.0	9.0	W
Intermodulation Distortion	IMD		-	-	-30	dB

Note : Above parameters , ratings , limits and conditions are subject to change.